

L Number	Hits	Search Text	DB	Time stamp
1	552268	((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:56
2	5165	((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 17:05
3	3108	((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:05
4	170	((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @ad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:07
5	151	((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @ad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:07
6	267	((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @ad<19930825) (((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @rlad<19930825)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:06
7	1055	((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) same ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:06

8	69	((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) same ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")) and @ad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:18
9	65	((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) same ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")) and @ad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:07
10	115	((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) same ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")) and @ad<19930825) (((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolating)) same ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")) and @rlad<19930825)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:07
11	85333	(rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (laser excimer excimer KrF ArF XeCl XeF)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:18
12	16995	((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) and ((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (laser excimer excimer KrF ArF XeCl XeF))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:18
13	770	((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating)) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane)) and ((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 (laser excimer excimer KrF ArF XeCl XeF))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:45

14	19	((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")) and ((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (laser eximer excimer KrF ArF XeCl XeF))) and @ad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:58
15	44	((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")) and ((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (laser eximer excimer KrF ArF XeCl XeF))) and @rlad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:19
16	52	((((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane)) and ((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (laser eximer excimer KrF ArF XeCl XeF))) and @ad<19930825) (((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane)) and ((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (laser eximer excimer KrF ArF XeCl XeF))) and @rlad<19930825)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:19
17	4	((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane)) and ((rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 (laser eximer excimer KrF ArF XeCl XeF))) and @rlad<19930825)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 16:49
18	17869	(rt a rtp rto anneal annealing annealed anneals annealling annealed heat heated heating bake baking baked thermal thermally thermaly) near15 ((remov\$4 eliminat\$4 reduc\$4 lessen\$4 decreas\$3) near3 (carbon organic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 17:03

24	7477	((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 ((remov\$4 eliminat\$4 reduc\$4 lessen\$4 decreas\$3) near3 (carbon organic)) and ((oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) near12 (carbon organic)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 17:04
25	58	((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 ((remov\$4 eliminat\$4 reduc\$4 lessen\$4 decreas\$3) near3 (carbon organic)) and ((oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) near12 (carbon organic))) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 17:05
26	3	(((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 ((remov\$4 eliminat\$4 reduc\$4 lessen\$4 decreas\$3) near3 (carbon organic)) and ((oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) near12 (carbon organic))) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @ad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 17:06
27	1	(((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 ((remov\$4 eliminat\$4 reduc\$4 lessen\$4 decreas\$3) near3 (carbon organic)) and ((oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) near12 (carbon organic))) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl ortho silicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @rlad<19930825	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 17:06
28	3	(((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 ((remov\$4 eliminat\$4 reduc\$4 lessen\$4 decreas\$3) near3 (carbon organic)) and ((oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) near12 (carbon organic))) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl orthosilicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @ad<19930825) (((((rt a rtp rto anneal annealing annealed anneals annealling annealled heat heated heating bake baking baked thermal thermally thermaly) near15 ((remov\$4 eliminat\$4 reduc\$4 lessen\$4 decreas\$3) near3 (carbon organic)) and ((oxide dioxide SiO SiO2 SiO?sub.? dielectric insulator insulating insulation isolation isolating) near12 (carbon organic))) and ((PCVD P-CVD PECVD PE-CVD PACVD PA-CVD plasma) near12 (TEOS tetraethylorthosilicate "tetra ethyl ortho silicate" "tetraethyl orthosilicate" "tetraethyl orthosilicate" tetraethoxysilane "tetra ethoxy silane" "tetraethoxy silane")))) and @rlad<19930825)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 17:06